

## 4-bit Single Chip Microcomputer



- Core CPU Architecture
- SVD Circuit
- R/F Converter for Temperature Measuring
- High Quality Display LCD Driver

### ■ DESCRIPTION

The E0C6251 is a single-chip microcomputer made up of the 4-bit core CPU E0C6200A, ROM, RAM, LCD driver, input ports, output ports, I/O ports, clock timer and A/D converter (R/F conversion type). Because of its low-voltage operation and low power consumption, this series is ideal for a wide range of applications, and is especially suitable for battery-driven systems.

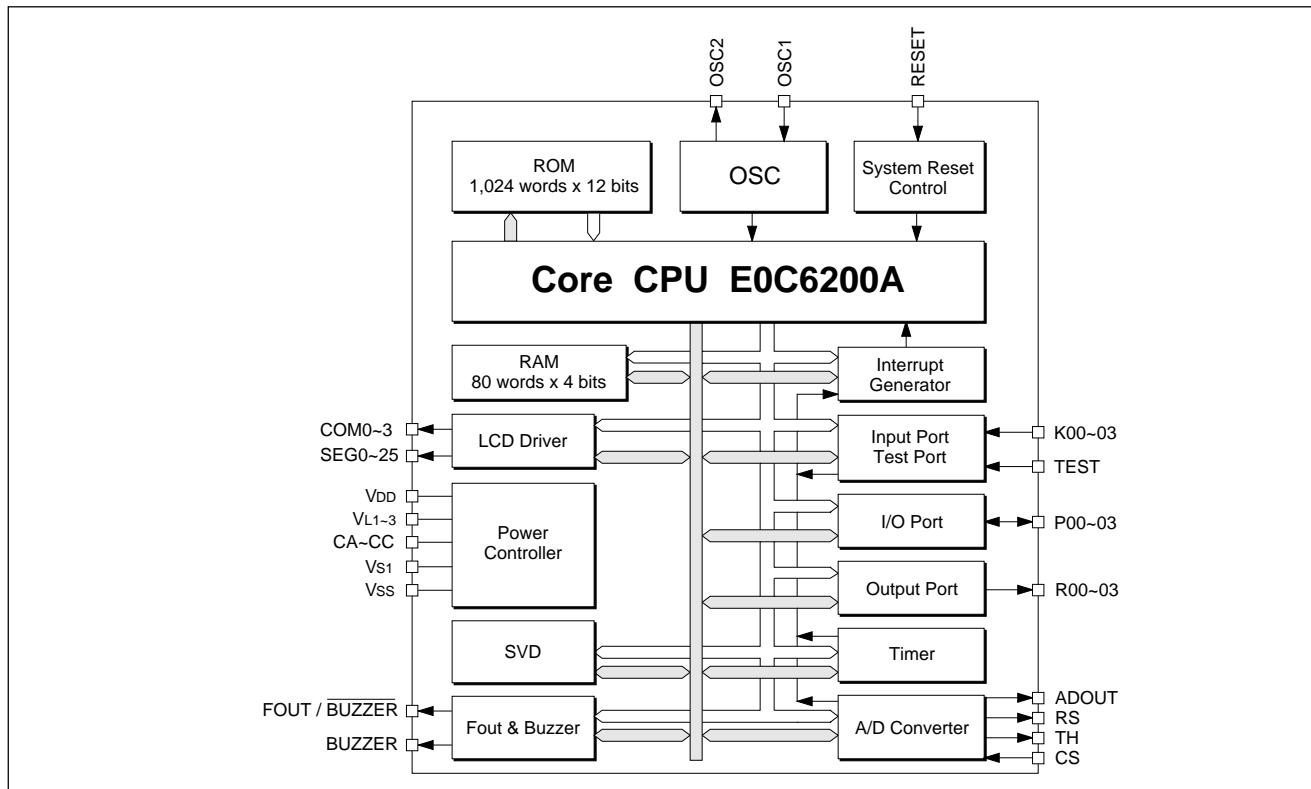
### ■ FEATURES

- CMOS LSI 4-bit parallel processing
- Clock ..... 32.768kHz (Typ.) (Crystal or CR oscillation)
- Instruction set ..... 100 instructions
- Instruction execution time ..... 153μsec, 214μsec, 366μsec (depending on instruction)
- ROM capacity ..... 1,024 × 12 bits
- RAM capacity ..... 80 × 4 bits
- Input port ..... 4 bits (pull-down resistors are available by mask option)
- Output port ..... 4 bits (common, BZ,  $\overline{BZ}$ , FOUT and LAMP ports are available by mask option)
- I/O port ..... 4 bits
- Large capacity output port ..... 2 bits
- Buzzer output port ..... 2 bits
- Clock output port ..... 1 bit
- A/D converter ..... R/F (resistance/frequency) conversion type, 1ch.
- LCD driver ..... 26 segments × 2/3/4 commons (Power regulator built-in. DC output available. Selected duty by software setting)
- R/F converter circuit ..... Temperature measurement is possible with the R/F converter in which a external thermistor. Range of temperature measurement and accuracy of temperature measurement changed by thermistor.
- Built-in supply voltage detection (SVD) circuit ..... 1ch.
- Timer ..... Clock timer : 1ch.
- Interrupts ..... External : Input interrupt 1 line  
Internal : Timer interrupt 1 line  
R/F converter interrupt 1 line
- Supply voltage ..... 1.5V (0.9 to 2.0V min. 1.0V: Measurement temperature mode)  
3.0V (1.8 to 3.5V)
- Current consumption ..... HALT mode : 1.0μA (Typ.)  
: 2.5μA (Typ.)  
OPERATING mode : 2.5μA (Typ.)  
: 5.0μA (Typ.)
- Package ..... QFP6-60pin (ceramic), QFP6-64pin (plastic)  
Die form

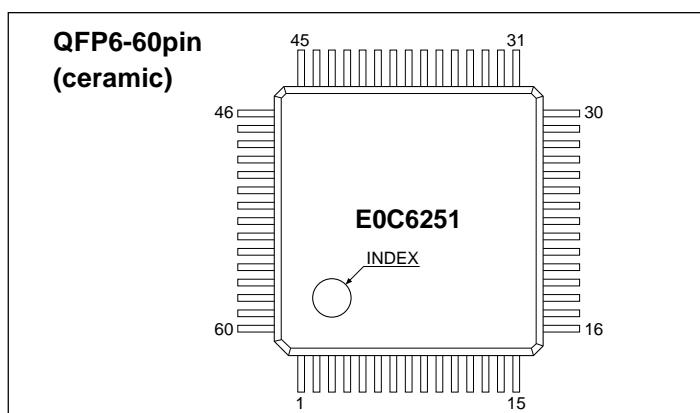
### ■ LINE UP

Model	Operating voltage	Clock
E0C62L51	0.9V to 2.0V	32.768kHz (Crystal or CR oscillation)
E0C6251	1.8V to 3.5V	32.768kHz (Crystal or CR oscillation)

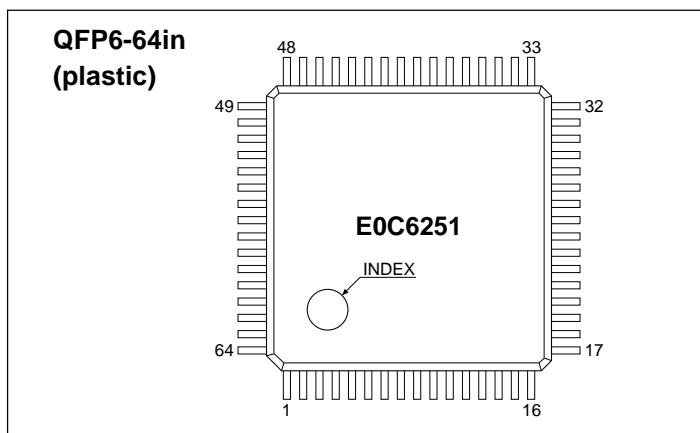
## ■ BLOCK DIAGRAM



## ■ PIN CONFIGURATION



No.	Pin name						
1	COM3	16	SEG13	31	P00	46	TH
2	SEG0	17	SEG14	32	P01	47	ADOUT
3	SEG1	18	SEG15	33	P02	48	VDD
4	SEG2	19	SEG16	34	P03	49	OSC1
5	SEG3	20	SEG17	35	RESET	50	OSC2
6	SEG4	21	SEG18	36	K00	51	Vss
7	SEG5	22	SEG19	37	K01	52	CA
8	SEG6	23	SEG20	38	K02	53	CB
9	SEG7	24	SEG21	39	K03	54	CC
10	SEG8	25	SEG22	40	R00	55	VL1
11	SEG9	26	SEG23	41	R01	56	VL2
12	SEG10	27	SEG24	42	R02	57	VL3
13	SEG11	28	SEG25	43	R03	58	COM0
14	SEG12	29	VDD	44	CS	59	COM1
15	TEST	30	Vs1	45	RS	60	COM2



No.	Pin name						
1	COM2	17	TEST	33	P00	49	CS
2	COM3	18	SEG13	34	P01	50	RS
3	N.C.	19	SEG14	35	P02	51	TH
4	SEG0	20	SEG15	36	P03	52	ADOUT
5	SEG1	21	SEG16	37	RESET	53	VDD
6	SEG2	22	SEG17	38	K00	54	OSC1
7	SEG3	23	SEG18	39	K01	55	OSC2
8	SEG4	24	SEG19	40	K02	56	Vss
9	SEG5	25	SEG20	41	K03	57	CA
10	SEG6	26	SEG21	42	R00	58	CB
11	SEG7	27	SEG22	43	R01	59	CC
12	SEG8	28	SEG23	44	R02	60	VL1
13	SEG9	29	SEG24	45	R03	61	VL2
14	SEG10	30	SEG25	46	N.C.	62	VL3
15	SEG11	31	VDD	47	N.C.	63	COM0
16	SEG12	32	Vs1	48	N.C.	64	COM1

N.C. = No Connection

## ■ PIN DESCRIPTION

Pin name	Pin No.		In/Out	Function
	QFP6-60pin	QFP6-64pin		
VDD	29, 48	31, 53	I	Power source (+) terminal
Vss	51	56	I	Power source (-) terminal
Vs1	30	32	O	Oscillation and internal logic system regulated voltage output terminal
VL1	55	60	O	LCD system regulated voltage output terminal (approx. -1.05 V)
VL2	56	61	O	LCD system booster output terminal (VL1 x 2)
VL3	57	62	O	LCD system booster output terminal (VL1 x 3)
CA-CC	52-54	57-59	-	Booster capacitor connecting terminal
OSC1	49	54	I	Crystal or CR oscillation input terminal
OSC2	50	55	O	Crystal or CR oscillation output terminal
K00-K03	36-39	38-41	I	Input terminal
P00-P03	31-34	33-36	I/O	I/O terminal
R00-R03	40-43	42-45	O	Output terminal
SEGO-25	2-14, 16-28	4-16, 18-30	O	LCD segment output terminal (Convertible to DC output by mask option)
COMO-3	58-60, 1	63, 64, 1, 2	O	LCD common output terminal
CS	44	49	I	A/D converter CR oscillation input terminal
RS	45	50	O	A/D converter CR oscillation output terminal
TH	46	51	O	A/D converter CR oscillation output terminal
ADOUT	47	52	O	A/D converter oscillation frequency output terminal
RESET	35	37	I	Initial reset input terminal
TEST	15	17	I	Test input terminal

## ■ ELECTRICAL CHARACTERISTICS

### ● Absolute Maximum Ratings

(VDD=0V)

Rating	Symbol	Value	Unit
Supply voltage	Vss	-5.0 to 0.5	V
Input voltage (1)	VI	Vss - 0.3 to 0.5	V
Input voltage (2)	Viosc	Vss - 0.3 to 0.5	V
Operating temperature	Topr	-20 to 70	°C
Storage temperature	Tstg	-65 to 150	°C
Soldering temperature / Time	Tsol	260°C, 10sec (lead section)	-
Permissible dissipation *1	PD	250	mW

\*1: In case of plastic package (QFP6-64pin).

### ● Recommended Operating Conditions

Condition	Symbol	Remark	Min.	Typ.	Max.	Unit
Supply voltage	Vss	VDD=0V	-3.5	-3.0	-1.8	V
Oscillation frequency	fosc1	Crystal oscillation		32.768		kHz
	fosc2	CR oscillation, R=420kΩ		65	80	kHz
Booster capacitor (1)	C1		0.1			μF
Booster capacitor (2)	C2		0.1			μF
Capacitor between VDD and VL1	C3		0.1			μF
Capacitor between VDD and VL2	C4		0.1			μF
Capacitor between VDD and VL3	C5		0.1			μF
Capacitor between VDD and Vs1	C6		0.1			μF

### E0C62L51

(Ta=-20 to 70°C)

Condition	Symbol	Remark	Min.	Typ.	Max.	Unit
Supply voltage	Vss	VDD=0V *3	-2.0	-1.5	-1.1	V
		VDD=0V, With software control *1	-2.0	-1.5	-0.9 *2	V
Oscillation frequency	fosc1	Crystal oscillation		32.768		kHz
		CR oscillation, R=420kΩ		65	80	kHz
Booster capacitor (1)	C1		0.1			μF
Booster capacitor (2)	C2		0.1			μF
Capacitor between VDD and VL1	C3		0.1			μF
Capacitor between VDD and VL2	C4		0.1			μF
Capacitor between VDD and VL3	C5		0.1			μF
Capacitor between VDD and Vs1	C6		0.1			μF

\*1: When the heavy load protection mode is set by software and the SVD circuit is turned off.

\*2: The voltage which can be displayed on the LCD panel will differ according to the characteristics of the LCD panel.

\*3: When there is no software control during CR oscillation or crystal oscillation.

## ● DC Characteristics

### E0C6251

(Unless otherwise specified: VDD=0V, VSS=-3.0V, fosc=32.768kHz, Ta=25°C, Vs1/VL1–VL3 are internal voltage, C1–C6=0.1μF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
High level input voltage (1)	VIH1	K00–K03, P00–P03	0.2•VSS		0	V
High level input voltage (2)	VIH2	RESET, TEST	0.15•VSS		0	V
Low level input voltage (1)	VIL1	K00–K03, P00–P03	VSS		0.8•VSS	V
Low level input voltage (2)	VIL2	RESET, TEST	VSS		0.85•VSS	V
High level input current (1)	IIH1	VIH1=0V, No pull down resistor	K00–K03, P00–P03	0	0.5	μA
High level input current (2)	IIH2	VIH2=0V, With pull down resistor	K00–K03	5	16	μA
High level input current (3)	IIH3	VIH3=0V, With pull down resistor	P00–P03 RESET, TEST	30	100	μA
Low level input current	IIL	VIL=VSS	K00–K03, P00–P03 RESET, TEST	-0.5	0	μA
High level output current (1)	IOH1	VOH1=0.1•VSS	R02, R03, P00–P03		-1.0	mA
High level output current (2)	IOH2	VOH2=0.1•VSS (built-in protection resistance)	R00, R01		-1.0	mA
High level output current (3)	IOH3	VOH3=-1.0V	ADOUT	-100	-10	μA
Low level output current (1)	IOL1	VOL1=0.9•VSS	R02, R03, P00–P03	3.0		mA
Low level output current (2)	IOL2	VOL2=0.9•VSS (built-in protection resistance)	R00, R01	3.0		mA
Low level output current (3)	IOL3	VOL3=-2.0V	ADOUT	10	100	μA
Common output current	IOH4	VOH4=-0.05V	COM0–COM3		-3	μA
	IOL4	VOL4=VL3+0.05V		3		μA
Segment output current (during LCD output)	IOH5	VOH5=-0.05V	SEG0–SEG25		-3	μA
	IOL5	VOL5=VL3+0.05V		3		μA
Segment output current (during DC output)	IOH6	VOH6=0.1•VSS	SEG0–SEG25		-300	μA
	IOL6	VOL6=0.9•VSS		300		μA

### E0C62L51

(Unless otherwise specified: VDD=0V, VSS=-1.5V, fosc=32.768kHz, Ta=25°C, Vs1/VL1–VL3 are internal voltage, C1–C6=0.1μF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
High level input voltage (1)	VIH1	K00–K03, P00–P03	0.2•VSS		0	V
High level input voltage (2)	VIH2	RESET, TEST	0.15•VSS		0	V
Low level input voltage (1)	VIL1	K00–K03, P00–P03	VSS		0.8•VSS	V
Low level input voltage (2)	VIL2	RESET, TEST	VSS		0.85•VSS	V
High level input current (1)	IIH1	VIH1=0V, No pull down resistor	K00–K03, P00–P03	0	0.5	μA
High level input current (2)	IIH2	VIH2=0V, With pull down resistor	K00–K03	2.0	16	μA
High level input current (3)	IIH3	VIH3=0V, With pull down resistor	P00–P03 RESET, TEST	9.0	100	μA
Low level input current	IIL	VIL=VSS	K00–K03, P00–P03 RESET, TEST	-0.5	0	μA
High level output current (1)	IOH1	VOH1=0.1•VSS	R02, R03, P00–P03		-200	μA
High level output current (2)	IOH2	VOH2=0.1•VSS (built-in protection resistance)	R00, R01		-200	μA
High level output current (3)	IOH3	VOH3=-1.0V	ADOUT	-100	-10	μA
Low level output current (1)	IOL1	VOL1=0.9•VSS	R02, R03, P00–P03	700		μA
Low level output current (2)	IOL2	VOL2=0.9•VSS (built-in protection resistance)	R00, R01	700		μA
Low level output current (3)	IOL3	VOL3=-2.0V	ADOUT	10	100	μA
Common output current	IOH4	VOH4=-0.05V	COM0–COM3		-3	μA
	IOL4	VOL4=VL3+0.05V		3		μA
Segment output current (during LCD output)	IOH5	VOH5=-0.05V	SEG0–SEG25		-3	μA
	IOL5	VOL5=VL3+0.05V		3		μA
Segment output current (during DC output)	IOH6	VOH6=0.1•VSS	SEG0–SEG25		-100	μA
	IOL6	VOL6=0.9•VSS		130		μA

## ● Analog Circuit Characteristics and Current Consumption

### E0C6251 (Normal Mode)

(Unless otherwise specified: V<sub>DD</sub>=0V, V<sub>SS</sub>=-3.0V, fosc=32.768kHz, Ta=25°C, C<sub>G</sub>=25pF, V<sub>S1</sub>/V<sub>L1</sub>-V<sub>L3</sub> are internal voltage, C<sub>1</sub>-C<sub>6</sub>=0.1μF)  
(During A/D conversion: RS=49.8kΩ, TH=50kΩ, CS=2,200pF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Internal voltage	V <sub>L1</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L1</sub> (without panel load)	-1.15	-1.05	-0.95	V
	V <sub>L2</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L2</sub> (without panel load)	2•V <sub>L1</sub> -0.1		2•V <sub>L1</sub> ×0.9	V
	V <sub>L3</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L3</sub> (without panel load)	3•V <sub>L1</sub> -0.1		3•V <sub>L1</sub> ×0.9	V
SVD voltage	V <sub>SVD</sub>		-2.55	-2.40	-2.25	V
SVD circuit response time	t <sub>SVD</sub>				100	μS
Current consumption	I <sub>OP</sub>	During HALT		1.0	2.5	μA
		During execution *1		2.5	5.0	μA
		During A/D conversion (HALT)		30	40	μA

\*1: The SVD circuit is turned off.

### E0C6251 (Heavy Load Protection Mode)

(Unless otherwise specified: V<sub>DD</sub>=0V, V<sub>SS</sub>=-3.0V, fosc=32.768kHz, Ta=25°C, C<sub>G</sub>=25pF, V<sub>S1</sub>/V<sub>L1</sub>-V<sub>L3</sub> are internal voltage, C<sub>1</sub>-C<sub>6</sub>=0.1μF)  
(During A/D conversion: RS=49.8kΩ, TH=50kΩ, CS=2,200pF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Internal voltage	V <sub>L1</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L1</sub> (without panel load)	-1.15	-1.05	-0.95	V
	V <sub>L2</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L2</sub> (without panel load)	2•V <sub>L1</sub> -0.1		2•V <sub>L1</sub> ×0.85	V
	V <sub>L3</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L3</sub> (without panel load)	3•V <sub>L1</sub> -0.1		3•V <sub>L1</sub> ×0.85	V
SVD voltage	V <sub>SVD</sub>		-2.55	-2.40	-2.25	V
SVD circuit response time	t <sub>SVD</sub>				100	μS
Current consumption	I <sub>OP</sub>	During HALT		2.0	5.5	μA
		During execution *1		5.5	10.0	μA
		During A/D conversion (HALT)		31	41.5	μA

\*1: The SVD circuit is turned off.

### E0C62L51 (Normal Mode)

(Unless otherwise specified: V<sub>DD</sub>=0V, V<sub>SS</sub>=-1.5V, fosc=32.768kHz, Ta=25°C, C<sub>G</sub>=25pF, V<sub>S1</sub>/V<sub>L1</sub>-V<sub>L3</sub> are internal voltage, C<sub>1</sub>-C<sub>6</sub>=0.1μF)  
(During A/D conversion: RS=49.8kΩ, TH=50kΩ, CS=2,200pF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Internal voltage	V <sub>L1</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L1</sub> (without panel load)	-1.15	-1.05	-0.95	V
	V <sub>L2</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L2</sub> (without panel load)	2•V <sub>L1</sub> -0.1		2•V <sub>L1</sub> ×0.9	V
	V <sub>L3</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L3</sub> (without panel load)	3•V <sub>L1</sub> -0.1		3•V <sub>L1</sub> ×0.9	V
SVD voltage	V <sub>SVD</sub>		-1.30	-1.20	-1.10	V
SVD circuit response time	t <sub>SVD</sub>				100	μS
Current consumption	I <sub>OP</sub>	During HALT		1.0	2.5	μA
		During execution *1		2.5	5.0	μA
		During A/D conversion (HALT)		30	40	μA

\*1: The SVD circuit is turned off.

### E0C62L51 (Heavy Load Protection Mode)

(Unless otherwise specified: V<sub>DD</sub>=0V, V<sub>SS</sub>=-1.5V, fosc=32.768kHz, Ta=25°C, C<sub>G</sub>=25pF, V<sub>S1</sub>/V<sub>L1</sub>-V<sub>L3</sub> are internal voltage, C<sub>1</sub>-C<sub>6</sub>=0.1μF)  
(During A/D conversion: RS=49.8kΩ, TH=50kΩ, CS=2,200pF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Internal voltage	V <sub>L1</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L1</sub> (without panel load)	-1.15	-1.05	-0.95	V
	V <sub>L2</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L2</sub> (without panel load)	2•V <sub>L1</sub> -0.1		2•V <sub>L1</sub> ×0.85	V
	V <sub>L3</sub>	Connect 1MΩ load resistor between V <sub>DD</sub> and V <sub>L3</sub> (without panel load)	3•V <sub>L1</sub> -0.1		3•V <sub>L1</sub> ×0.85	V
SVD voltage	V <sub>SVD</sub>		-1.30	-1.20	-1.10	V
SVD circuit response time	t <sub>SVD</sub>				100	μS
Current consumption	I <sub>OP</sub>	During HALT		2.0	5.5	μA
		During execution *1		5.5	10.0	μA
		During A/D conversion (HALT)		31	41.5	μA

\*1: The SVD circuit is turned off.

**E0C6251 (CR, Normal Mode)**(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=65kHz, RCR=420kΩ, Ta=25°C, Vs1/VL1–VL3 are internal voltage, C1–C6=0.1μF)  
(During A/D conversion: RS=49.8kΩ, TH=50kΩ, CS=2,200pF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Internal voltage	VL1	Connect 1MΩ load resistor between VDD and VL1 (without panel load)	-1.15	-1.05	-0.95	V
	VL2	Connect 1MΩ load resistor between VDD and VL2 (without panel load)	2•VL1 -0.1		2•VL1 ×0.9	V
	VL3	Connect 1MΩ load resistor between VDD and VL3 (without panel load)	3•VL1 -0.1		3•VL1 ×0.9	V
SVD voltage	V <sub>SVD</sub>		-2.55	-2.40	-2.25	V
SVD circuit response time	t <sub>SVD</sub>				100	μS
Current consumption	I <sub>OP</sub>	During HALT During execution *1 During A/D conversion (HALT)		8.0 15.0 37	15.0 20.0 52.5	μA

\*1: The SVD circuit is turned off.

**E0C6251 (CR, Heavy Load Protection Mode)**(Unless otherwise specified: VDD=0V, Vss=-3.0V, fosc=65kHz, RCR=420kΩ, Ta=25°C, Vs1/VL1–VL3 are internal voltage, C1–C6=0.1μF)  
(During A/D conversion: RS=49.8kΩ, TH=50kΩ, CS=2,200pF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Internal voltage	VL1	Connect 1MΩ load resistor between VDD and VL1 (without panel load)	-1.15	-1.05	-0.95	V
	VL2	Connect 1MΩ load resistor between VDD and VL2 (without panel load)	2•VL1 -0.1		2•VL1 ×0.85	V
	VL3	Connect 1MΩ load resistor between VDD and VL3 (without panel load)	3•VL1 -0.1		3•VL1 ×0.85	V
SVD voltage	V <sub>SVD</sub>		-2.55	-2.40	-2.25	V
SVD circuit response time	t <sub>SVD</sub>				100	μS
Current consumption	I <sub>OP</sub>	During HALT During execution *1 During A/D conversion (HALT)		16.0 30.0 45	30.0 40.0 57.5	μA

\*1: The SVD circuit is turned off.

**E0C62L51 (CR, Normal Mode)**(Unless otherwise specified: VDD=0V, Vss=-1.5V, fosc=65kHz, RCR=420kΩ, Ta=25°C, Vs1/VL1–VL3 are internal voltage, C1–C6=0.1μF)  
(During A/D conversion: RS=49.8kΩ, TH=50kΩ, CS=2,200pF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Internal voltage	VL1	Connect 1MΩ load resistor between VDD and VL1 (without panel load)	-1.15	-1.05	-0.95	V
	VL2	Connect 1MΩ load resistor between VDD and VL2 (without panel load)	2•VL1 -0.1		2•VL1 ×0.9	V
	VL3	Connect 1MΩ load resistor between VDD and VL3 (without panel load)	3•VL1 -0.1		3•VL1 ×0.9	V
SVD voltage	V <sub>SVD</sub>		-1.30	-1.20	-1.10	V
SVD circuit response time	t <sub>SVD</sub>				100	μS
Current consumption	I <sub>OP</sub>	During HALT During execution *1 During A/D conversion (HALT)		8.0 15.0 37	15.0 20.0 52.5	μA

\*1: The SVD circuit is turned off.

**E0C62L51 (CR, Heavy Load Protection Mode)**(Unless otherwise specified: VDD=0V, Vss=-1.5V, fosc=65kHz, RCR=420kΩ, Ta=25°C, Vs1/VL1–VL3 are internal voltage, C1–C6=0.1μF)  
(During A/D conversion: RS=49.8kΩ, TH=50kΩ, CS=2,200pF)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Internal voltage	VL1	Connect 1MΩ load resistor between VDD and VL1 (without panel load)	-1.15	-1.05	-0.95	V
	VL2	Connect 1MΩ load resistor between VDD and VL2 (without panel load)	2•VL1 -0.1		2•VL1 ×0.85	V
	VL3	Connect 1MΩ load resistor between VDD and VL3 (without panel load)	3•VL1 -0.1		3•VL1 ×0.85	V
SVD voltage	V <sub>SVD</sub>		-1.30	-1.20	-1.10	V
SVD circuit response time	t <sub>SVD</sub>				100	μS
Current consumption	I <sub>OP</sub>	During HALT During execution *1 During A/D conversion (HALT)		16.0 30.0 45	30.0 40.0 57.5	μA

\*1: The SVD circuit is turned off.

### ● Oscillation Characteristics

The oscillation characteristics change depending on the conditions (components used, board pattern, etc.). Use the following characteristics as reference values.

#### E0C6251 (Crystal oscillation circuit)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, Crystal: C-002R (Cl=35kΩ), Cg=25pF, Cd=built-in, Ta=25°C)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Oscillation start voltage	Vsta	tsta≤5sec (Vss)	-1.8			V
Oscillation stop voltage	Vstp	tstp≤10sec (Vss)	-1.8			V
Built-in capacitance (drain)	Cd	Including the parasitic capacity inside the IC		20		pF
Frequency/voltage deviation	Δf/ΔV	Vss=-1.8 to -3.5V			5	ppm
Frequency/IC deviation	Δf/ΔIC		-10		10	ppm
Frequency adjustment range	Δf/ΔCg	Cg=5 to 25pF	40			ppm
Harmonic oscillation start voltage	Vhho	Cg=5pF (Vss)			-3.5	V
Permitted leak resistance	Rleak	Between OSC1 and VDD, Vss	200			MΩ

#### E0C62L51 (Crystal oscillation circuit)

(Unless otherwise specified: VDD=0V, Vss=-1.5V, Crystal: C-002R (Cl=35kΩ), Cg=25pF, Cd=built-in, Ta=25°C)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Oscillation start voltage	Vsta	tsta≤5sec (Vss)	-1.1			V
Oscillation stop voltage	Vstp	tstp≤10sec (Vss)	-1.1(-0.9)*1			V
Built-in capacitance (drain)	Cd	Including the parasitic capacity inside the IC		20		pF
Frequency/voltage deviation	Δf/ΔV	Vss=-1.1 to -2.0V (-0.9) *1			5	ppm
Frequency/IC deviation	Δf/ΔIC		-10		10	ppm
Frequency adjustment range	Δf/ΔCg	Cg=5 to 25pF	40			ppm
Harmonic oscillation start voltage	Vhho	Cg=5pF (Vss)			-2.0	V
Permitted leak resistance	Rleak	Between OSC1 and VDD, Vss	200			MΩ

\*1: Items enclosed in parentheses ( ) are those used when operating at heavy load protection mode.

#### E0C6251 (CR oscillation circuit)

(Unless otherwise specified: VDD=0V, Vss=-3.0V, Rcr=420kΩ, Ta=25°C)

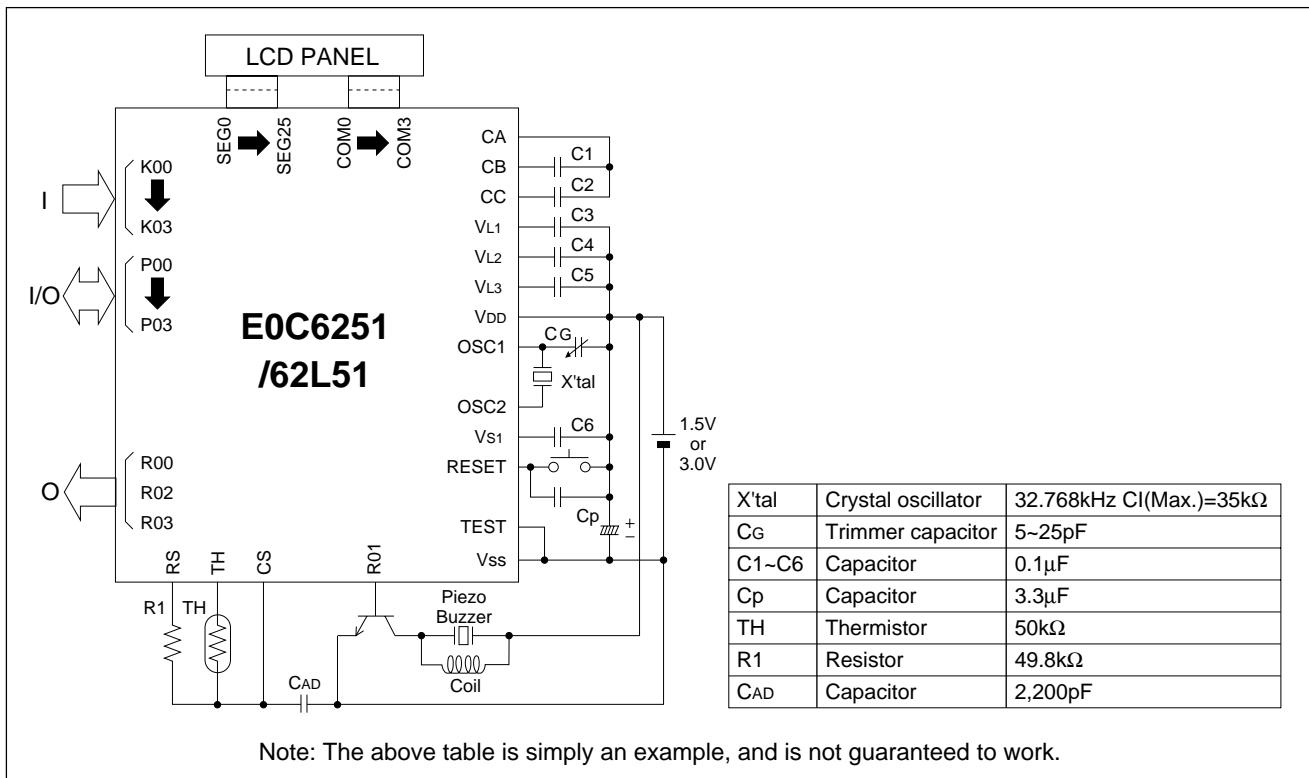
Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Oscillation frequency dispersion	fosc		-20	65kHz	20	%
Oscillation start voltage	Vsta		-1.8			V
Oscillation start time	tsta	Vss=-1.8 to -3.5V		3		mS
Oscillation stop voltage	Vstp		(Vss)	-1.8		V

#### E0C62L51 (CR oscillation circuit)

(Unless otherwise specified: VDD=0V, Vss=-1.5V, Rcr=420kΩ, Ta=25°C)

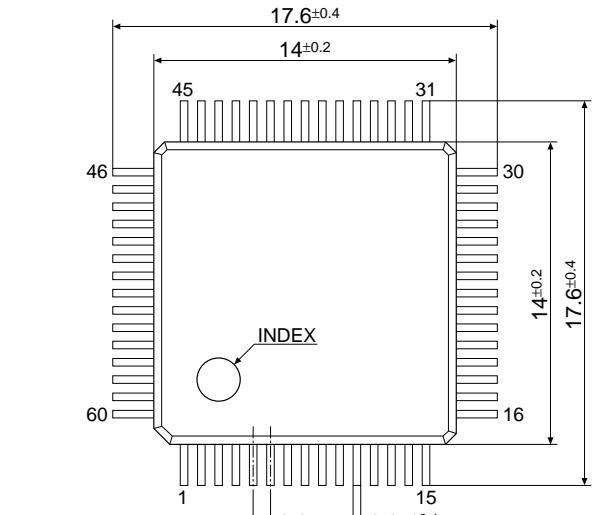
Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Oscillation frequency dispersion	fosc		-20	65kHz	20	%
Oscillation start voltage	Vsta		-1.1			V
Oscillation start time	tsta	Vss=-1.1 to -2.0V		3		mS
Oscillation stop voltage	Vstp		(Vss)	-1.1		V

## ■ BASIC EXTERNAL CONNECTION DIAGRAM

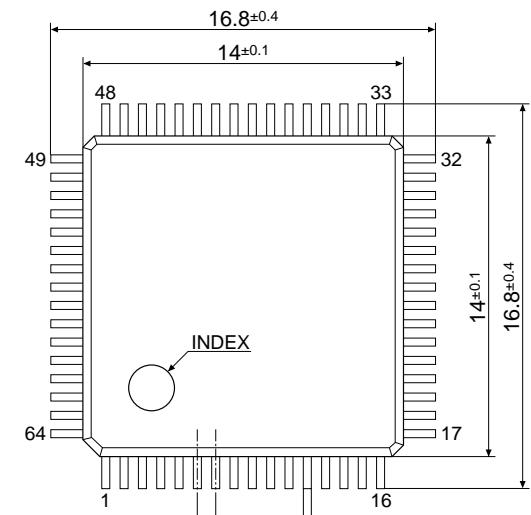


## ■ PACKAGE DIMENSIONS

**Ceramic QFP6-60pin**



**Plastic QFP6-64pin**



Unit: mm

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